



## Monolayer Graphene

Transparency: >97%

Graphene Coverage: 100% with sporadic adlayers (see optical image above)

FET mobility\*: >2700 cm<sup>2</sup>/(V·s)

Sheet resistance\*: 430 ± 50 Ω/sq

Grain size: >40 μm

Raman D/G ratio: Indistinguishable to 0.03

## Substrate

Our 8-inch(200mm) Si/SiO<sub>2</sub> wafers are sourced from a reliable, quality-assured supplier.

Type/Doping: P/B

Wafer Thickness : 725 +/- 25 μm

Oxide Thickness: 300 nm

Resistivity: 5 – 30 (ohm-cm)

Orientation: <1-0-0>

Growth Method: CZ

Metal Impurities: 1.00e10 – 5.00e10 (at/cm<sup>2</sup>)